

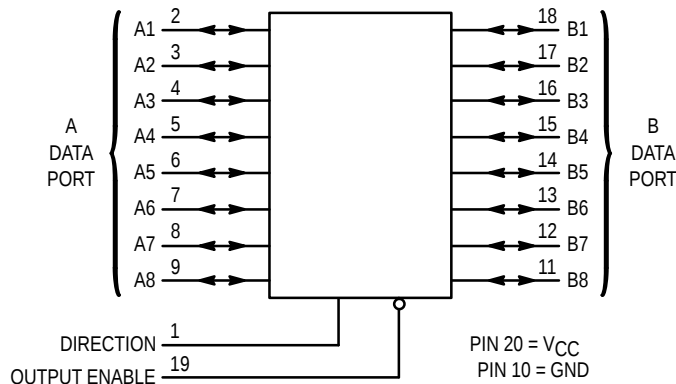
Octal 3-State Noninverting Bus Transceiver with LSTTL Compatible Inputs High-Performance Silicon-Gate CMOS

The MC54/74HCT245A is identical in pinout to the LS245. This device may be used as a level converter for interfacing TTL or NMOS outputs to High Speed CMOS inputs.

The MC54/74HCT245A is a 3-state noninverting transceiver that is used for 2-way asynchronous communication between data buses. The device has an active-low Output Enable pin, which is used to place the I/O ports into high-impedance states. The Direction control determines whether data flows from A to B or from B to A.

- Output Drive Capability: 15 LSTTL Loads
- TTL/NMOS Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μ A
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 304 FETs or 76 Equivalent Gates

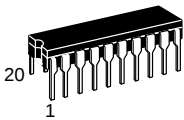
LOGIC DIAGRAM



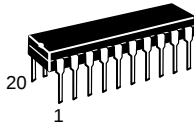
Design Criteria	Value	Units
Internal Gate Count*	76	ea
Internal Gate Propagation Delay	1.0	ns
Internal Gate Power Dissipation	5.0	μ W
Speed Power Product	0.005	pJ

* Equivalent to a two-input NAND gate.

MC54/74HCT245A



J SUFFIX
CERAMIC PACKAGE
CASE 732-03



N SUFFIX
PLASTIC PACKAGE
CASE 738-03



DW SUFFIX
SOIC PACKAGE
CASE 751D-04



SD SUFFIX
SSOP PACKAGE
CASE 940C-03



DT SUFFIX
TSSOP PACKAGE
CASE 948E-02

ORDERING INFORMATION

MC54HCTXXXAJ	Ceramic
MC74HCTXXXAN	Plastic
MC74HCTXXXADW	SOIC
MC74HCTXXXASD	SSOP
MC74HCTXXXADT	TSSOP

PIN ASSIGNMENT

DIRECTION	1	20	V _{CC}
A1	2	19	OUTPUT ENABLE
A2	3	18	B1
A3	4	17	B2
A4	5	16	B3
A5	6	15	B4
A6	7	14	B5
A7	8	13	B6
A8	9	12	B7
GND	10	11	B8

FUNCTION TABLE

Control Inputs		Operation
Output Enable	Direction	
L	L	Data Transmitted from Bus B to Bus A
L	H	Data Transmitted from Bus A to Bus B
H	X	Buses Isolated (High-Impedance State)

X = Don't Care



MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	– 0.5 to + 7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	– 0.5 to $V_{CC} + 0.5$	V
V_{out}	DC Output Voltage (Referenced to GND)	– 0.5 to $V_{CC} + 0.5$	V
I_{in}	DC Input Current, per Pin	± 20	mA
I_{out}	DC Output Current, per Pin	± 35	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 75	mA
P_D	Power Dissipation in Still Air, Plastic or Ceramic DIP† SOIC Package† SSOP or TSSOP Package†	750 500 450	mW
T_{stg}	Storage Temperature	– 65 to + 150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC, SSOP or TSSOP Package) (Ceramic DIP)	260 300	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

* Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

† Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C
Ceramic DIP: – 10 mW/°C from 100° to 125°C
SOIC Package: – 7 mW/°C from 65° to 125°C
SSOP or TSSOP Package: – 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	– 55	+ 125	°C
t_r, t_f	Input Rise and Fall Time (Figure 1)	0	500	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				– 55 to 25°C	≤ 85°C	≤ 125°C	
V_{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \leq 20 \mu\text{A}$	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V_{IL}	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \leq 20 \mu\text{A}$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V_{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \leq 20 \mu\text{A}$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \leq 6.0 \text{ mA}$	4.5	3.98	3.84	3.7	
V_{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \leq 20 \mu\text{A}$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \leq 6.0 \text{ mA}$	4.5	0.26	0.33	0.4	
I_{in}	Maximum Input Leakage Current	$V_{in} = V_{CC} \text{ or GND, Pins 1 or 19}$	5.5	± 0.1	± 1.0	± 1.0	μA

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit
				- 55 to 25°C	≤ 85°C	≤ 125°C	
I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	5.5	4.0	40	160	μA
I _{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State V _{in} = V _{IL} or V _{IH} V _{out} = V _{CC} or GND, I/O Pins	5.5	± 0.5	± 5.0	± 10	μA
ΔI _{CC}	Additional Quiescent Supply Current	V _{in} = 2.4 V, Any One Input V _{in} = V _{CC} or GND, Other Inputs I _{out} = 0 μA	5.5	≥ -55°C	25°C to 125°C		mA
				2.9	2.4		

NOTE: Information on typical parametric values can be found in Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (V_{CC} = 5.0 V ± 10%, C_L = 50 pF, Input t_r = t_f = 6.0 ns)

Symbol	Parameter	Guaranteed Limit			Unit
		- 55 to 25°C	≤ 85°C	≤ 125°C	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to B or B to A (Figures 1 and 3)	22	28	33	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to A or B (Figures 2 and 4)	30	36	42	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to A or B (Figures 2 and 4)	30	36	42	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, any Output (Figures 1 and 3)	12	15	18	ns
C _{in}	Maximum Input Capacitance (Pin 1 or 19)	10	10	10	pF
C _{out}	Maximum Three-State I/O Capacitance, (I/O in High-Impedance State)	15	15	15	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

C _{PD}	Power Dissipation Capacitance (Per Enabled Output)*	Typical @ 25°C, V _{CC} = 5.0 V		pF
		97		

* Used to determine the no-load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

SWITCHING WAVEFORMS

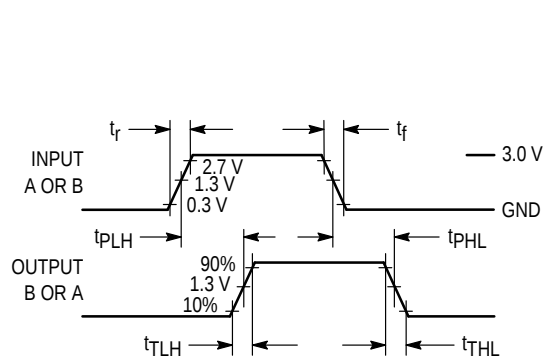


Figure 1.

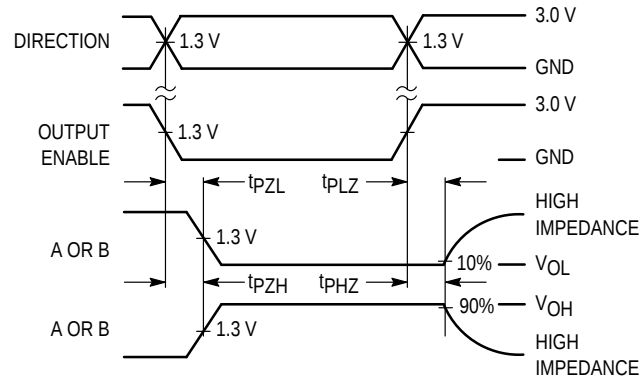
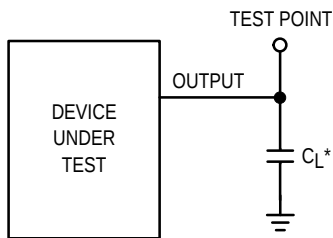
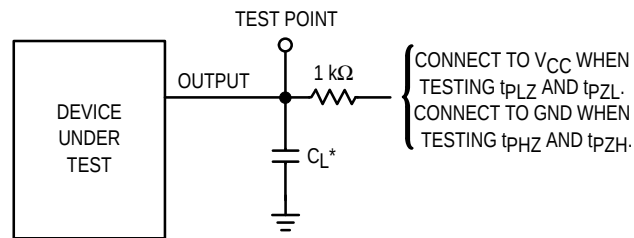


Figure 2.



* Includes all probe and jig capacitance

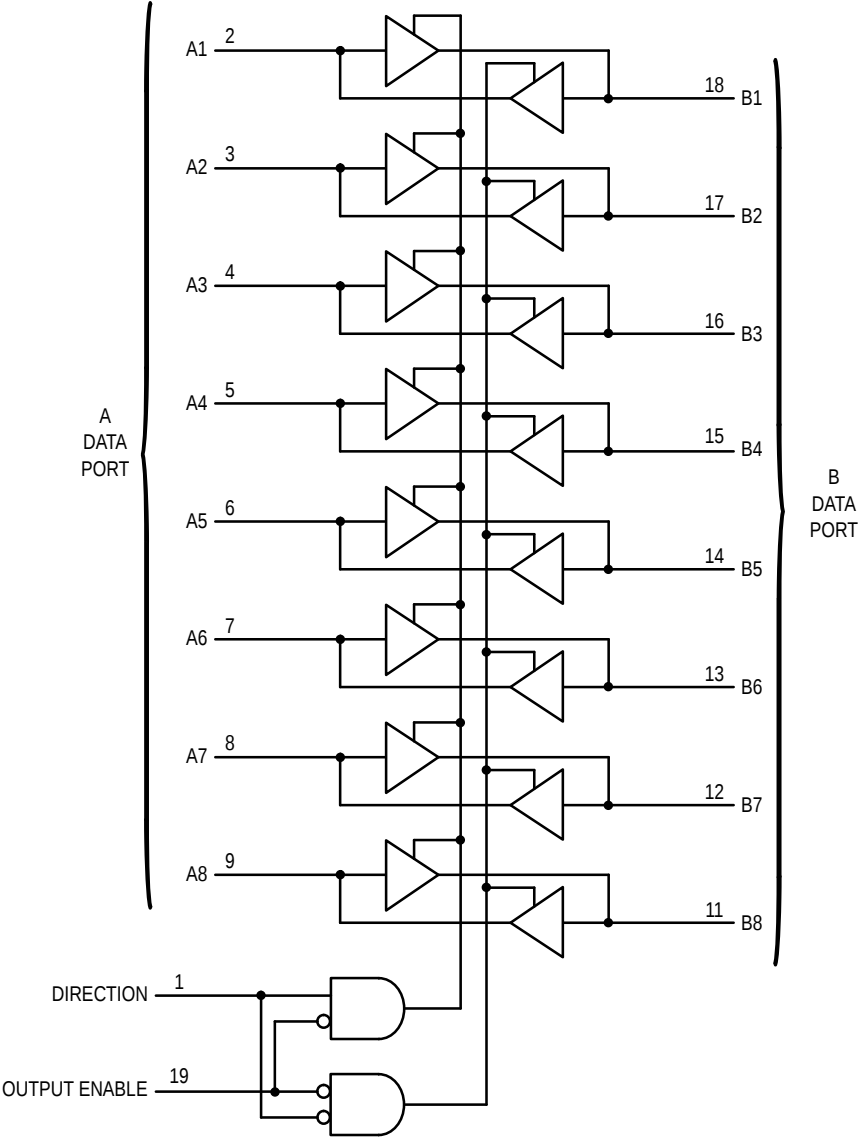
Figure 3.



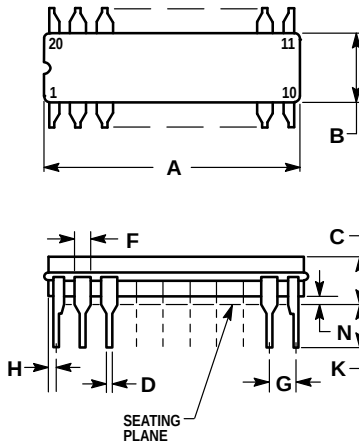
* Includes all probe and jig capacitance

Figure 4. Test Circuit

EXPANDED LOGIC DIAGRAM



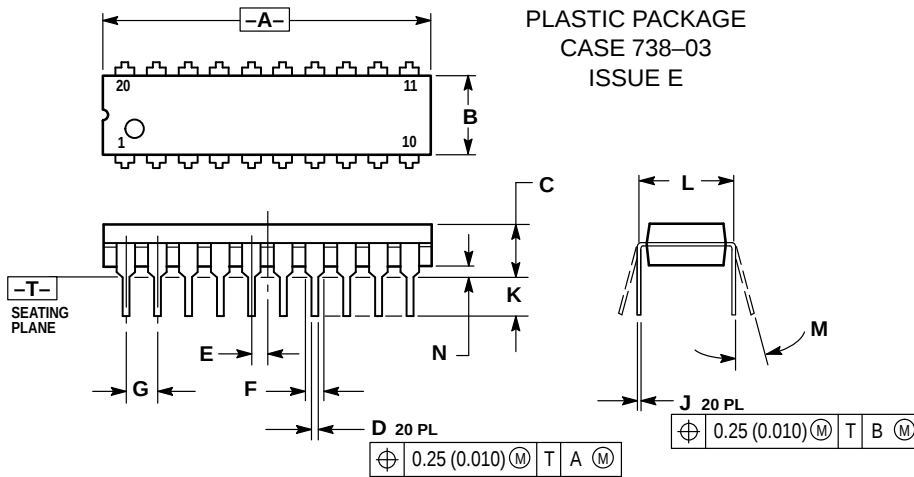
OUTLINE DIMENSIONS

J SUFFIX
 CERAMIC PACKAGE
 CASE 732-03
 ISSUE E


NOTES:

- LEADS WITHIN 0.25 (0.010) DIAMETER, TRUE POSITION AT SEATING PLANE, AT MAXIMUM MATERIAL CONDITION.
- DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
- DIMENSIONS A AND B INCLUDE MENISCUS.

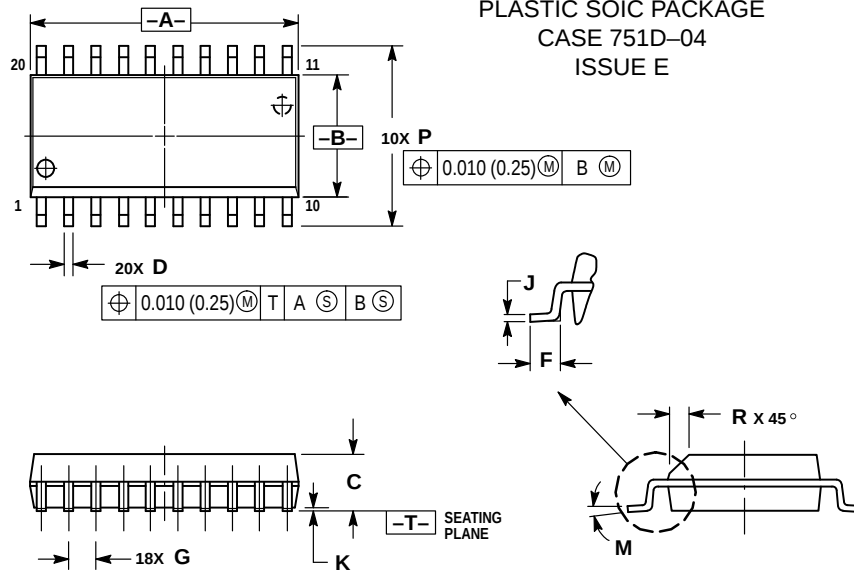
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	23.88	25.15	0.940	0.990
B	6.60	7.49	0.260	0.295
C	3.81	5.08	0.150	0.200
D	0.38	0.56	0.015	0.022
F	1.40	1.65	0.055	0.065
G	2.54 BSC		0.100 BSC	
H	0.51	1.27	0.020	0.050
J	0.20	0.30	0.008	0.012
K	3.18	4.06	0.125	0.160
L	7.62 BSC		0.300 BSC	
M	0°	15°	0°	15°
N	0.25	1.02	0.010	0.040

N SUFFIX
 PLASTIC PACKAGE
 CASE 738-03
 ISSUE E


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
- DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
- DIMENSION B DOES NOT INCLUDE MOLD FLASH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.010	1.070	25.66	27.17
B	0.240	0.260	6.10	6.60
C	0.150	0.180	3.81	4.57
D	0.015	0.022	0.39	0.55
E	0.050 BSC		1.27 BSC	
F	0.050	0.070	1.27	1.77
G	0.100 BSC		2.54 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.140	2.80	3.55
L	0.300 BSC		7.62 BSC	
M	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01

DW SUFFIX
 PLASTIC SOIC PACKAGE
 CASE 751D-04
 ISSUE E


NOTES:

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